

SS8550D

Plastic-Encapsulate Transistors

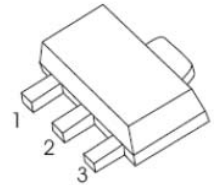
TRANSISTOR (PNP)

FEATURES

Complimentto SS8050

MARKING: Y2

SOT-89-3L



1. BASE

2. COLLECTOR

3. EMITTER

MAXIMUM RATINGS (Ta=25°C unless otherwise noted)

Symbol	Parameter	Value	Unit
V_{CBO}	Collector-Base Voltage	-40	V
V_{CEO}	Collector-Emitter Voltage	-25	V
V_{EBO}	Emitter-Base Voltage	-5	V
I_C	Collector Current -Continuous	-1.5	A
P_C	Collector Power Dissipation	0.5	W
$R_{\theta JA}$	Thermal Resistance From Junction To Ambient	250	°C/W
T_J, T_{stg}	Operation Junction and Storage Temperature Range	-55~150	°C

ELECTRICAL CHARACTERISTICS (Ta=25°C unless otherwise specified)

Parameter	Symbol	Test conditions	Min	Max	Unit
Collector-base breakdown voltage	$V_{(BR)CBO}$	$I_C = -100\mu A, I_E = 0$	-40		V
Collector-emitter breakdown voltage	$V_{(BR)CEO}$	$I_C = -0.1mA, I_B = 0$	-25		V
Emitter-base breakdown voltage	$V_{(BR)EBO}$	$I_E = -100\mu A, I_C = 0$	-5		V
Collector cut-off current	I_{CBO}	$V_{CB} = -40V, I_E = 0$		-0.1	μA
Collector cut-off current	I_{CEO}	$V_{CE} = -20V, I_B = 0$		-0.5	μA
Emitter cut-off current	I_{EBO}	$V_{EB} = -5V, I_C = 0$		-0.1	μA
DC current gain	$h_{FE(1)}$	$V_{CE} = -1V, I_C = -100mA$	200	350	
	$h_{FE(2)}$	$V_{CE} = -1V, I_C = -800mA$	40		
Collector-emitter saturation voltage	$V_{CE(sat)}$	$I_C = -800mA, I_B = -80mA$		-0.5	V
Base-emitter saturation voltage	$V_{BE(sat)}$	$I_C = -800mA, I_B = -80mA$		-1.2	V
Base-emitter on voltage	$V_{BE(on)}$	$I_C = -1V, V_{CE} = -10mA$		-1	V
Base-emitter positive favor voltage	V_{BEF}	$I_B = -1A$		-1.55	V
Transition frequency	f_T	$V_{CE} = -10V, I_C = -50mA$	100		MHz
output capacitance	C_{ob}	$V_{CB} = -10V, I_E = 0, f = 1MHz$		20	pF

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